FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790CB

Generic Copy

Issue Date: 12-Dec-2012

TITLE: Final PCN for wafer fab transfer from Gunma to the ON Semiconductor wafer fabrication site ISMF in Seremban, Malaysia. (Group CB)

PROPOSED FIRST SHIP DATE: starting on 15-Mar-2013 until 30-Apr-2013 (the actual ship date will be different by each product, please check with the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact your local ON Semiconductor Sales Office or Toshikazu.Hirai@onsemi.com

SAMPLES: Contact your local ON Semiconductor Sales Office or Katsuya.Ito@onsemi.com

ADDITIONAL RELIABILITY DATA: May be available
Contact your local ON Semiconductor Sales Office or Yasuhiro.Igarashi@onsemi.com.

NOTIFICATION TYPE:
Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce the transfer of products from Sanyo wafer fabrication site located in Gunma to the ON Semiconductor wafer fabrication site ISMF in Seremban, Malaysia.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

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RELIABILITY DATA SUMMARY

Group CB

Test:	Conditions:	Interval:	Results
Steady State Operating Life (This test isn't performed for diodes)	Tj=150degC	1000 hrs	Pass
High Temperature Reverse Bias	Ta=125/150degC,VR/VCES=max	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 125/150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC,2.03×10^{5}Pa,100%	50 hrs	Pass
High Temperature Storage	Ta=125/150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Solder Test	Ta=260degC±5degC,	10 s	Pass

Notice) ※1 Pre-treatment: Resistance to Soldering heat (Flow: 260degC/10s)

ELECTRICAL CHARACTERISTIC SUMMARY

There is no change in the electrical performance. Datasheet specifications remain unchanged.

CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of affected Generic parts:

Group CB

PART_ID
2SA2112-AN
2SA2125-TD-E
2SA2126-TL-E
2SD1048-7-TB-E
CPH3122-TL-E
RD0306T-H
SB01-15C-TB-E
SB02-09C-TB-E
SB07-03C-TB-E
SB10-05P-TD-E